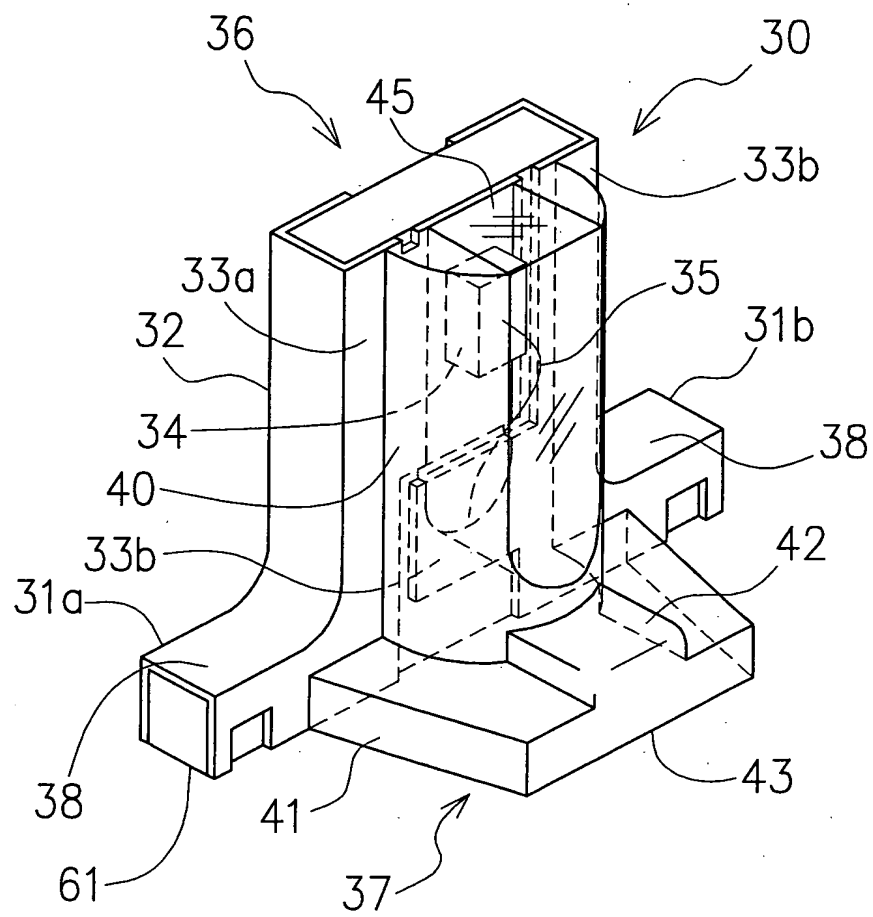


Fig. 1





This diagram shows a cross-sectional view of a semiconductor device. The main body is a substrate 50. On top of it is a gate stack 36, which includes a gate dielectric 30 and a gate electrode 37. Below the gate stack is a channel layer 37. To the left and right of the channel are source and drain regions 41. A contact pad 52a is formed on the surface of the drain region. A dashed line indicates a cross-section through the center of the device.

# Fig. 4

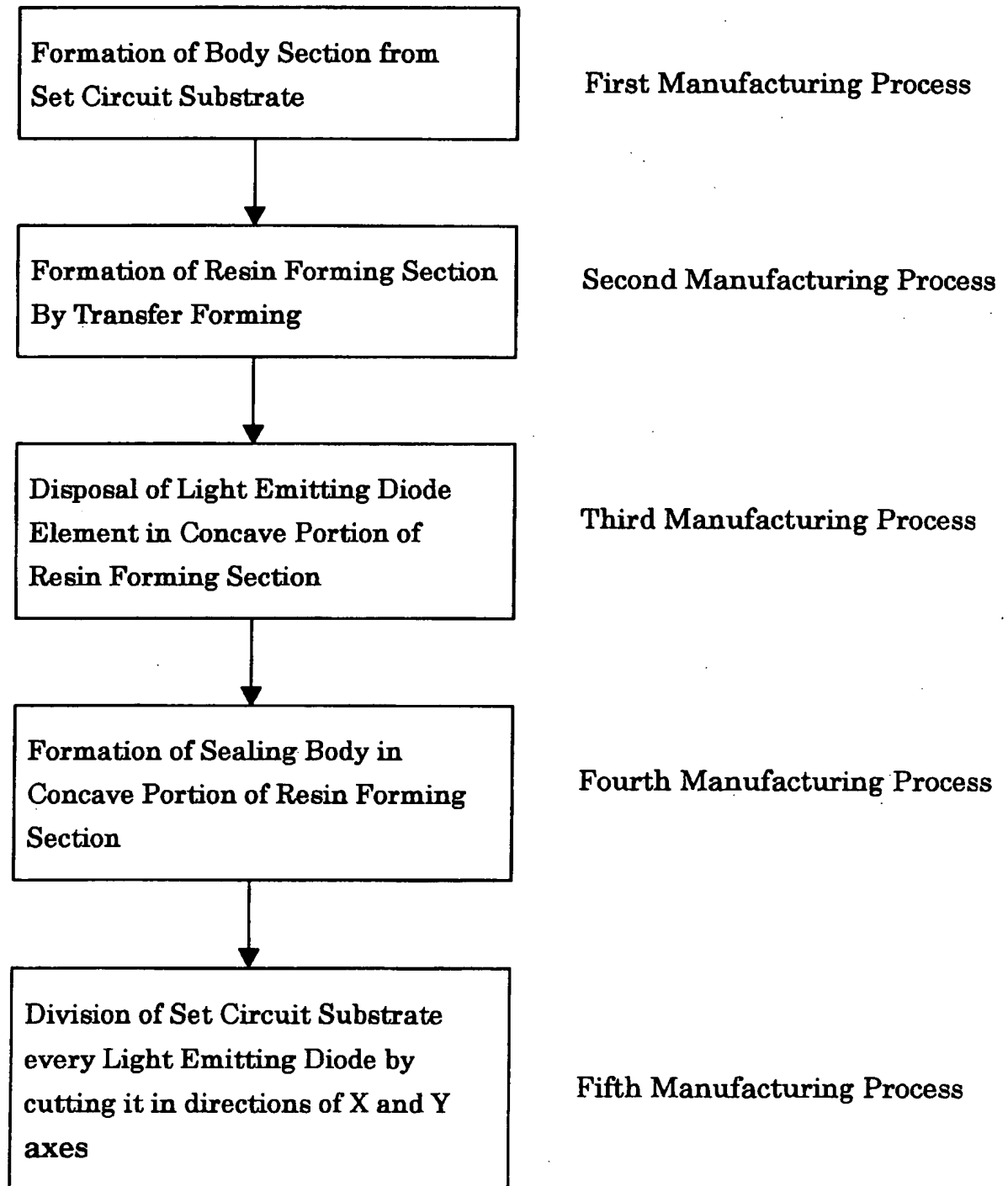


Fig. 5

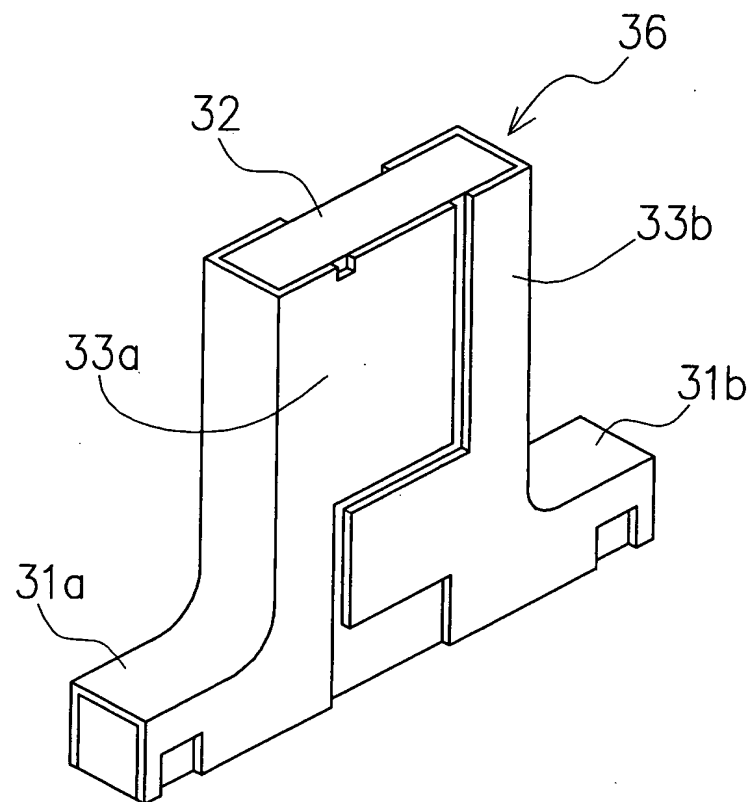


Fig. 6

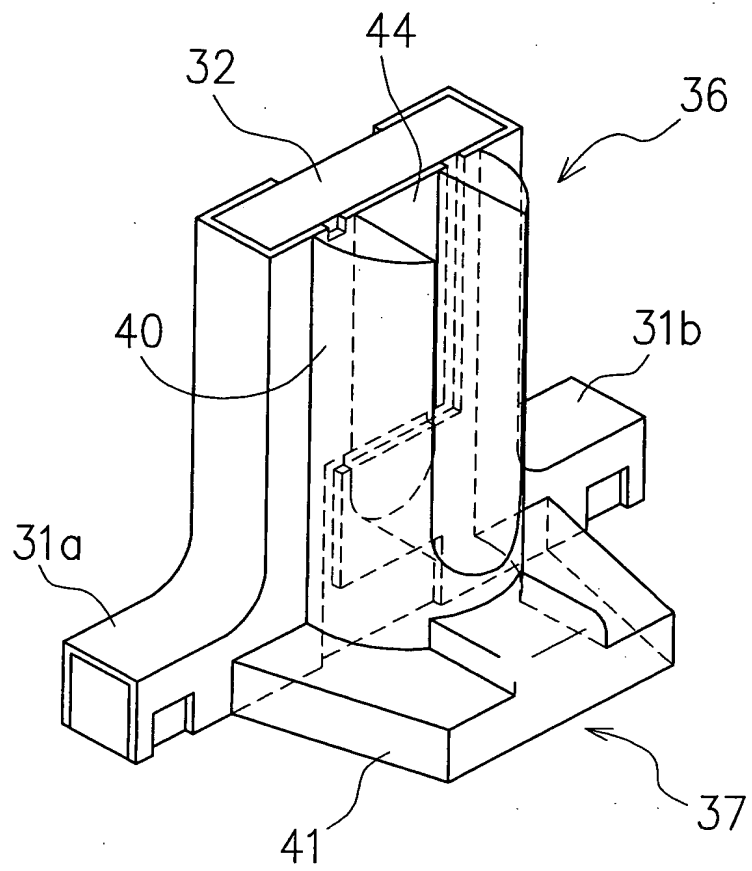


Fig. 7

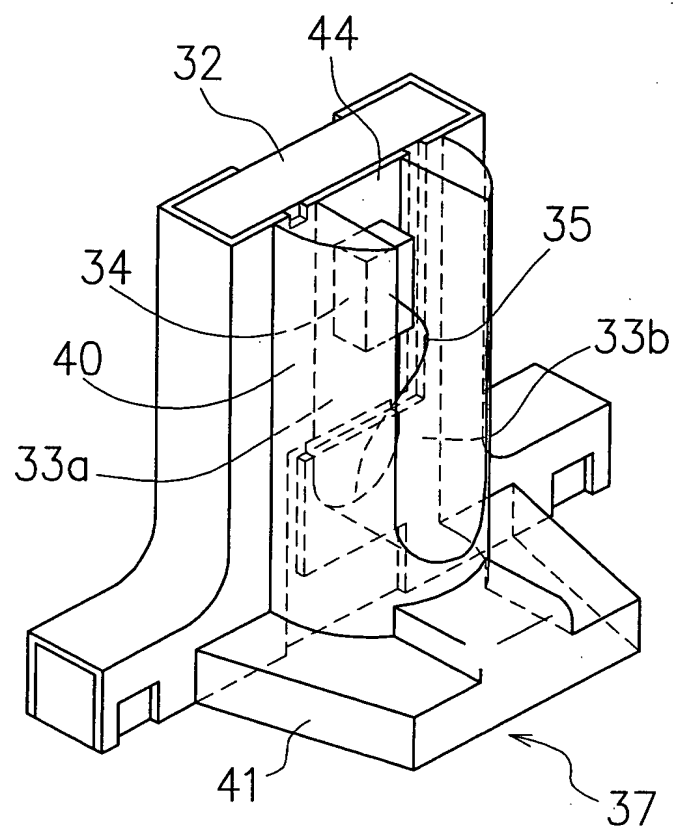






Fig. 9  
(Prior Art)

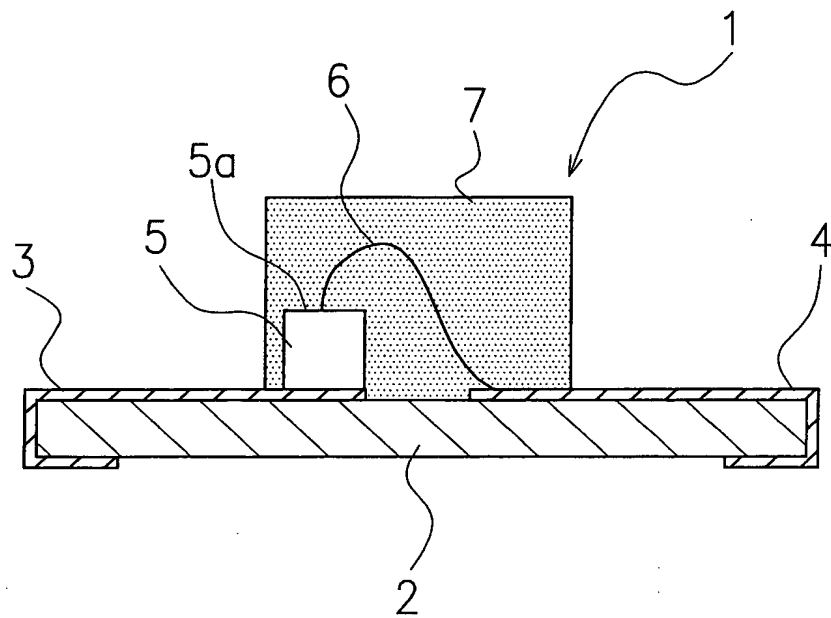


Fig. 10  
(Prior Art)

